DISTINCTIVE CHARACTERISTICS

- Fast access time
  - Speed options as fast as 55 ns
- Low power consumption
  - 20 µA typical CMOS standby current
- JEDEC-approved pinout
- Single +5 V power supply
- ±10% power supply tolerance standard
- 100% Flashrite™ programming
  - Typical programming time of 8 seconds
- Latch-up protected to 100 mA from -1 V to VCC + 1 V
- High noise immunity
- Versatile features for simple interfacing
  - Both CMOS and TTL input/output compatibility
  - Two line control functions
- Standard 28-pin DIP, PDIP, and 32-pin PLCC packages

GENERAL DESCRIPTION

The Am27C512 is a 512-Kbit, ultraviolet erasable programmable read-only memory. It is organized as 64K words by 8 bits per word, operates from a single +5 V supply, has a static standby mode, and features fast single address location programming. Products are available in windowed ceramic DIP packages, as well as plastic one time programmable (OTP) PDIP and PLCC packages.

Data can be typically accessed in less than 55 ns, allowing high-performance microprocessors to operate without any WAIT states. The device offers separate Output Enable (OE#) and Chip Enable (CE#) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 80 mW in active mode, and 100 µW in standby mode.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random. The device supports AMD's Flashrite programming algorithm (100 µs pulses), resulting in a typical programming time of 8 seconds.

BLOCK DIAGRAM
PRODUCT SELECTOR GUIDE

<table>
<thead>
<tr>
<th>Family Part Number</th>
<th>Am27C512</th>
</tr>
</thead>
<tbody>
<tr>
<td>Speed Options</td>
<td>-55</td>
</tr>
<tr>
<td>V_{CC} = 5.0 V ± 5%</td>
<td>-70</td>
</tr>
<tr>
<td>V_{CC} = 5.0 V ± 10%</td>
<td>-90</td>
</tr>
<tr>
<td>Max Access Time (ns)</td>
<td>-120</td>
</tr>
<tr>
<td>55</td>
<td>-150</td>
</tr>
<tr>
<td>70</td>
<td>-200</td>
</tr>
<tr>
<td>90</td>
<td>50</td>
</tr>
<tr>
<td>120</td>
<td>50</td>
</tr>
<tr>
<td>150</td>
<td>50</td>
</tr>
<tr>
<td>200</td>
<td>50</td>
</tr>
<tr>
<td>250</td>
<td></td>
</tr>
</tbody>
</table>

CE# (E#) Access (ns) 55 70 90 120 150 200 250
OE# (G#) Access (ns) 35 40 40 50 50 50 50

CONNECTION DIAGRAMS

Top View

DIP

PLCC

Notes:
1. JEDEC nomenclature is in parenthesis.
2. Don’t use (DU) for PLCC.

PIN DESIGNATIONS
A0–A15 = Address Inputs
CE# (E#) = Chip Enable Input
DQ0–DQ7 = Data Input/Outputs
OE# (G#)/V_{PP} = Output Enable Input
Program Voltage Input
V_{CC} = V_{CC} Supply Voltage
V_{SS} = Ground
NC = No Internal Connection

LOGIC SYMBOL
ORDERING INFORMATION
UV EPROM Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of the following:

AM27C512 -55 D C 5 B

- **OPTIONAL PROCESSING**
  - Blank = Standard Processing
  - B = Burn-In

- **VOLTAGE TOLERANCE**
  - $V_{CC} = 5\%$
  - See Product Selector Guide and Valid Combinations

- **TEMPERATURE RANGE**
  - C = Commercial ($0^\circ$C to +70°C)
  - I = Industrial ($-40^\circ$C to +85°C)
  - E = Extended ($-55^\circ$C to +125°C)

- **PACKAGE TYPE**
  - D = 28-Pin Ceramic DIP (CDV028)

- **SPEED OPTION**
  - See Product Selector Guide and Valid Combinations

**DEVICE NUMBER/DESCRIPTION**

Am27C512
512 Kilobit (64 K x 8-Bit) CMOS UV EPROM

<table>
<thead>
<tr>
<th>Valid Combinations</th>
<th>Valid Combinations</th>
</tr>
</thead>
<tbody>
<tr>
<td>AM27C512-55 $V_{CC} = 5.0$ V ± 5%</td>
<td>DC5</td>
</tr>
<tr>
<td>AM27C512-55 $V_{CC} = 5.0$ V ± 10%</td>
<td>DC, DCB</td>
</tr>
<tr>
<td>AM27C512-70</td>
<td>DC, DCB, DI, DIB</td>
</tr>
<tr>
<td>AM27C512-90</td>
<td>DC, DCB, DI, DIB</td>
</tr>
<tr>
<td>AM27C512-120</td>
<td>DC, DCB, DI, DIB, DE, DEB</td>
</tr>
<tr>
<td>AM27C512-150</td>
<td>DC, DCB, DI, DIB, DE, DEB</td>
</tr>
<tr>
<td>AM27C512-200</td>
<td>DC, DCB, DI, DIB</td>
</tr>
<tr>
<td>AM27C512-255 $V_{CC} = 5.0$ V ± 5%</td>
<td>DC, DCB, DI, DIB</td>
</tr>
</tbody>
</table>

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.
ORDERING INFORMATION
OTP EPROM Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of the following:

| AM27C512 | -55 | P | C | 5 | B |

OPTIONAL PROCESSING
Blank = Standard Processing

VOLTAGE TOLERANCE
5 = $V_{CC} \pm 5\%$
See Product Selector Guide and Valid Combinations

TEMPERATURE RANGE
C = Commercial ($0^\circ C$ to $+70^\circ C$)
I = Industrial ($-40^\circ C$ to $+85^\circ C$)
E = Extended ($-55^\circ C$ to $+125^\circ C$)

PACKAGE TYPE
P = 28-Pin Plastic DIP (PD 028)
J = 32-Pin Plastic Leaded Chip Carrier (PL 032)

SPEED OPTION
See Product Selector Guide and Valid Combinations

DEVICE NUMBER/DESCRIPTION
Am27C512
512 Kliobit (64 K x 8-Bit) CMOS OTP EPROM

<table>
<thead>
<tr>
<th>Valid Combinations</th>
</tr>
</thead>
<tbody>
<tr>
<td>AM27C512-55 $V_{CC} = 5.0 , V \pm 5%$</td>
</tr>
<tr>
<td>AM27C512-55 $V_{CC} = 5.0 , V \pm 10%$</td>
</tr>
<tr>
<td>AM27C512-70</td>
</tr>
<tr>
<td>AM27C512-90</td>
</tr>
<tr>
<td>AM27C512-120</td>
</tr>
<tr>
<td>AM27C512-150</td>
</tr>
<tr>
<td>AM27C512-200</td>
</tr>
<tr>
<td>AM27C512-255 $V_{CC} = 5.0 , V \pm 5%$</td>
</tr>
</tbody>
</table>

Valid Combinations
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.
FUNCTIONAL DESCRIPTION

Device Erasure

In order to clear all locations of their programmed contents, the device must be exposed to an ultraviolet light source. A dosage of 15 W seconds/cm² is required to completely erase the device. This dosage can be obtained by exposure to an ultraviolet lamp—wavelength of 2537 Å—with intensity of 12,000 µW/cm² for 15 to 20 minutes. The device should be directly under and about one inch from the source, and all filters should be removed from the UV light source prior to erasure.

Note that all UV erasable devices will erase with light sources having wavelengths shorter than 4000 Å, such as fluorescent light and sunlight. Although the erasure process happens over a much longer time period, exposure to any light source should be prevented for maximum system reliability. Simply cover the package window with an opaque label or substance.

Device Programming

Upon delivery, or after each erasure, the device has all of its bits in the "ONE", or HIGH state. "ZEROs" are loaded into the device through the programming procedure.

The device enters the programming mode when 12.75 V ± 0.25 V is applied to the OE#/VPP pin, and CE# is at VIL.

For programming, the data to be programmed is applied 8 bits in parallel to the data pins.

The flowchart in the Programming section of the EPROM Products Data Book (Section 5, Figure 5-1) shows AMD's Flashrite algorithm. The Flashrite algorithm reduces programming time by using a 100 µs programming pulse and by giving each address only as many pulses to reliably program the data. After each pulse is applied to a given address, the data in that address is verified. If the data does not verify, additional pulses are given until it verifies or the maximum pulses allowed is reached. This process is repeated while sequencing through each address of the device. This part of the algorithm is done at VCC = 6.25 V to assure that each EPROM bit is programmed to a sufficiently high threshold voltage. After the final address is completed, the entire EPROM memory is verified at VCC = VPP = 5.25 V.

Please refer to Section 5 of the EPROM Products Data Book for additional programming information and specifications.

Program Inhibit

Programming different data to multiple devices in parallel is easily accomplished. Except for CE#, all like inputs of the devices may be common. A TTL low-level program pulse applied to one device's CE# input with OE#/VPP = 12.75 V ± 0.25 V, will program that particular device. A high-level CE# input inhibits the other devices from being programmed.

Program Verify

A verification should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with OE#/VPP and CE# at VIL and VPP between 12.5 V and 13.0 V.

Autoselect Mode

The autoselect mode provides manufacturer and device identification through identifier codes on DQ0–DQ7. This mode is primarily intended for programming equipment to automatically match a device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ± 5°C ambient temperature range that is required when programming the device.

To activate this mode, the programming equipment must force VIL on address line A9. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from VIL to VIH (that is, changing the address from 00h to 01h). All other address lines must be held at VIL during the autoselect mode.

Byte 0 (A0 = VIL) represents the manufacturer code, and Byte 1 (A0 = VIL), the device identifier code. Both codes have odd parity, with DQ7 as the parity bit.

Read Mode

To obtain data at the device outputs, Chip Enable (CE#) and Output Enable (OE#/VPP) must be driven low. CE# controls the power to the device and is typically used to select the device. OE#/VPP enables the device to output data, independent of device selection. Addresses must be stable for at least tACC–tOE. Refer to the Switching Waveforms section for the timing diagram.

Standby Mode

The device enters the CMOS standby mode when CE# is at VCC ± 0.3 V. Maximum VCC current is reduced to 100 µA. The device enters the TTL-standby mode when CE# is at VIH. Maximum VCC current is reduced to 1.0 mA. When in either standby mode, the device places its outputs in a high-impedance state, independent of the OE# input.

Output OR-Tieing

To accommodate multiple memory connections, a two-line control function provides:

- Low memory power dissipation, and
- Assurance that output bus contention will not occur.
CE# should be decoded and used as the primary device-selecting function, while OE#/V_{PP} be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

**System Applications**

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 μF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between V_{CC} and V_{SS} to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 μF bulk electrolytic capacitor should be used between V_{CC} and V_{SS} for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

### MODE SELECT TABLE

<table>
<thead>
<tr>
<th>Mode</th>
<th>CE#</th>
<th>OE#/V_{PP}</th>
<th>A0</th>
<th>A9</th>
<th>Outputs</th>
</tr>
</thead>
<tbody>
<tr>
<td>Read</td>
<td>V_{IL}</td>
<td>V_{IL}</td>
<td>X</td>
<td>X</td>
<td>D_{OUT}</td>
</tr>
<tr>
<td>Output Disable</td>
<td>X</td>
<td>V_{IH}</td>
<td>X</td>
<td>X</td>
<td>High Z</td>
</tr>
<tr>
<td>Standby (TTL)</td>
<td>V_{IH}</td>
<td>X</td>
<td>X</td>
<td>X</td>
<td>High Z</td>
</tr>
<tr>
<td>Standby (CMOS)</td>
<td>V_{CC} ± 0.3 V</td>
<td>X</td>
<td>X</td>
<td>X</td>
<td>High Z</td>
</tr>
<tr>
<td>Program</td>
<td>V_{IL}</td>
<td>V_{PP}</td>
<td>X</td>
<td>X</td>
<td>D_{IN}</td>
</tr>
<tr>
<td>Program Verify</td>
<td>V_{IL}</td>
<td>V_{IL}</td>
<td>X</td>
<td>X</td>
<td>D_{OUT}</td>
</tr>
<tr>
<td>Program Inhibit</td>
<td>V_{IH}</td>
<td>V_{PP}</td>
<td>X</td>
<td>X</td>
<td>High Z</td>
</tr>
<tr>
<td>Autoselect (Note 3)</td>
<td>Manufacturer Code</td>
<td>V_{IL}</td>
<td>V_{IL}</td>
<td>V_{IL}</td>
<td>V_{H}</td>
</tr>
<tr>
<td></td>
<td>Device Code</td>
<td>V_{IL}</td>
<td>V_{IL}</td>
<td>V_{IH}</td>
<td>V_{H}</td>
</tr>
</tbody>
</table>

**Notes:**
1. V_{H} = 12.0 V ± 0.5 V.
2. X = Either V_{IH} or V_{IL}.
3. A1–A8 and A10–15 = V_{IL}.
4. See DC Programming Characteristics for V_{PP} voltage during programming.
ABSOLUTE MAXIMUM RATINGS

Storage Temperature
OTP Products ........................................... –65°C to +125°C
All Other Products .............................. –65°C to +150°C

Ambient Temperature
with Power Applied ............................... –55°C to +125°C
Voltage with Respect to V_SS (Note 1)
All pins except A9, V_PP, V_CC .......................... –0.6 V to V_CC + 0.6 V
A9 and V_PP (Note 2) .............................. –0.6 V to 13.5 V
V_CC ............................................. –0.6 V to 7.0 V

Notes:
1. Minimum DC voltage on input or I/O pins –0.5 V. During voltage transitions, the input may overshoot V_SS to –2.0 V for periods of up to 20 ns. Maximum DC voltage on input and I/O pins is V_CC + 0.5 V. During voltage transitions, input and I/O pins may overshoot to V_CC + 2.0 V for periods up to 20 ns.
2. Minimum DC input voltage on A9 is –0.5 V. During voltage transitions, A9 and V_PP may overshoot V_SS to –2.0 V for periods of up to 20 ns. A9 and V_PP must not exceed +13.5 V at any time.

Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices
Ambient Temperature (T_A) .......................... 0°C to +70°C

Industrial (I) Devices
Ambient Temperature (T_A) .......................... –40°C to +85°C

Extended (E) Devices
Ambient Temperature (T_A) .......................... –55°C to +125°C

Supply Read Voltages
V_CC for ± 5% devices .............................. +4.75 V to +5.25 V
V_CC for ± 10% devices .............................. +4.50 V to +5.50 V

Operating ranges define those limits between which the functionality of the device is guaranteed.
DC CHARACTERISTICS over operating range (unless otherwise specified)

<table>
<thead>
<tr>
<th>Parameter Symbol</th>
<th>Parameter Description</th>
<th>Test Conditions</th>
<th>Min</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>( V_{OH} )</td>
<td>Output HIGH Voltage</td>
<td>( I_{OH} = -400 \ \mu A )</td>
<td>2.4</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>( V_{OL} )</td>
<td>Output LOW Voltage</td>
<td>( I_{OL} = 2.1 \ \text{mA} )</td>
<td>0.45</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>( V_{IH} )</td>
<td>Input HIGH Voltage</td>
<td></td>
<td>2.0</td>
<td>( V_{CC} + 0.5 )</td>
<td>V</td>
</tr>
<tr>
<td>( V_{IL} )</td>
<td>Input LOW Voltage</td>
<td></td>
<td>-0.5</td>
<td>+0.8</td>
<td>V</td>
</tr>
<tr>
<td>( I_{LI} )</td>
<td>Input Load Current</td>
<td>( V_{IN} = 0 \ \text{V to} \ \ V_{CC} )</td>
<td>1.0</td>
<td></td>
<td>( \mu \text{A} )</td>
</tr>
<tr>
<td>( I_{LO} )</td>
<td>Output Leakage Current</td>
<td>( V_{OUT} = 0 \ \text{V to} \ \ V_{CC} )</td>
<td>C/I Devices</td>
<td>1.0</td>
<td>( \mu \text{A} )</td>
</tr>
<tr>
<td>( I_{CC1} )</td>
<td>( V_{CC} ) Active Current (Note 2)</td>
<td>( CE# = V_{IL}, f = 10 \ \text{MHz}, I_{OUT} = 0 \ \text{mA} )</td>
<td>25</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>( I_{DC2} )</td>
<td>( V_{CC} ) TTL Standby Current</td>
<td>( CE# = V_{IH} )</td>
<td>1.0</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>( I_{CC3} )</td>
<td>( V_{CC} ) CMOS Standby Current</td>
<td>( CE# = V_{CC} \pm 0.3 \ \text{V} )</td>
<td>100</td>
<td></td>
<td>( \mu \text{A} )</td>
</tr>
</tbody>
</table>

**Caution:** The device must not be removed from (or inserted into) a socket when \( V_{CC} \) or \( V_{PP} \) is applied.

**Notes:**
1. \( V_{CC} \) must be applied simultaneously or before \( V_{PP} \) and removed simultaneously or after \( V_{PP} \)
2. \( I_{CC1} \) is tested with \( OE# = V_{IH} \) to simulate open outputs.
3. Minimum DC Input Voltage is \(-0.5 \ \text{V}\). During transitions, the inputs may overshoot to \(-2.0 \ \text{V}\) for periods less than 20 ns. Maximum DC Voltage on output pins is \( V_{CC} \pm 0.5 \ \text{V}\), which may overshoot to \( V_{CC} \pm 2.0 \ \text{V}\) for periods less than 20 ns.

---

**Figure 1.** Typical Supply Current vs. Frequency
\( V_{CC} = 5.5 \ \text{V}, \ T = 25^\circ \text{C} \)

**Figure 2.** Typical Supply Current vs. Temperature
\( V_{CC} = 5.5 \ \text{V}, f = 10 \ \text{MHz} \)
TEST CONDITIONS

Table 1. Test Specifications

<table>
<thead>
<tr>
<th>Test Condition</th>
<th>Test Condition</th>
<th>-55</th>
<th>All others</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Output Load</td>
<td>Output Load</td>
<td>1</td>
<td>TTL gate</td>
<td></td>
</tr>
<tr>
<td>Output Load Capacitance, C_L</td>
<td>C_L</td>
<td>30</td>
<td>100</td>
<td>pF</td>
</tr>
<tr>
<td>(including jig capacitance)</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Rise and Fall Times</td>
<td>Input Rise</td>
<td>≤ 20</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>Input Pulse Levels</td>
<td>Input Pulse</td>
<td>0.0–3.0</td>
<td>0.45–2.4</td>
<td>V</td>
</tr>
<tr>
<td>Input timing measurement reference levels</td>
<td>Input timing measurement reference levels</td>
<td>1.5</td>
<td>0.8, 2.0</td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>Output timing</td>
<td>1.5</td>
<td>0.8, 2.0</td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>measurement</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>reference levels</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Note: Diodes are IN3064 or equivalents.

Figure 3. Test Setup

SWITCHING TEST WAVEFORM

Note: For $C_L = 30 \, \text{pF}$.

Note: For $C_L = 100 \, \text{pF}$.

KEY TO SWITCHING WAVEFORMS

<table>
<thead>
<tr>
<th>WAVEFORM</th>
<th>INPUTS</th>
<th>OUTPUTS</th>
</tr>
</thead>
<tbody>
<tr>
<td>Steady</td>
<td></td>
<td>Changing, State Unknown</td>
</tr>
<tr>
<td>Changing from H to L</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Changing from L to H</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Don’t Care, Any Change Permitted</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Does Not Apply</td>
<td></td>
<td>Center Line is High Impedance State (High Z)</td>
</tr>
</tbody>
</table>
AC CHARACTERISTICS

<table>
<thead>
<tr>
<th>Parameter Symbols</th>
<th>Standard</th>
<th>Description</th>
<th>Test Setup</th>
<th>Am27C512</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td>-55</td>
<td>-70</td>
</tr>
<tr>
<td>( t_{AVQV} )</td>
<td>( t_{ACC} )</td>
<td>Address to Output Delay</td>
<td>CE#, OE# = ( V_{IL} )</td>
<td>Max</td>
</tr>
<tr>
<td>( t_{ELQV} )</td>
<td>( t_{CE} )</td>
<td>Chip Enable to Output Delay</td>
<td>OE# = ( V_{IL} )</td>
<td>Max</td>
</tr>
<tr>
<td>( t_{GLQV} )</td>
<td>( t_{OE} )</td>
<td>Output Enable to Output Delay</td>
<td>CE# = ( V_{IL} )</td>
<td>Max</td>
</tr>
<tr>
<td>( t_{EHQZ} )</td>
<td>( t_{GHQZ} )</td>
<td>Chip Enable High or Output Enable High to Output High Z, Whichever Occurs First</td>
<td>Max</td>
<td>25</td>
</tr>
<tr>
<td>( t_{AXQX} )</td>
<td>( t_{OH} )</td>
<td>Output Hold Time from Addresses, CE# or OE#, Whichever Occurs First</td>
<td>Min</td>
<td>0</td>
</tr>
</tbody>
</table>

Caution: Do not remove the device from (or insert it into) a socket or board that has \( V_{PP} \) or \( V_{CC} \) applied.

Notes:
1. \( V_{CC} \) must be applied simultaneously or before \( V_{PP} \) and removed simultaneously or after \( V_{PP} \).
2. This parameter is sampled and not 100% tested.
3. Switching characteristics are over operating range, unless otherwise specified.
4. See Figure 3 and Table 1 for test specifications.

SWITCHING WAVEFORMS

Notes:
1. OE# may be delayed up to \( t_{ACC} - t_{OE} \) after the falling edge of the addresses without impact on \( t_{ACC} \).
2. \( t_{DF} \) is specified from OE# or CE#, whichever occurs first.

PACKAGE CAPACITANCE

<table>
<thead>
<tr>
<th>Parameter Symbol</th>
<th>Parameter Description</th>
<th>Test Conditions</th>
<th>CDV028</th>
<th>PL 032</th>
<th>PD 028</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td>Typ</td>
<td>Max</td>
<td>Typ</td>
</tr>
<tr>
<td>( C_{IN} )</td>
<td>Input Capacitance</td>
<td>( V_{IN} = 0 )</td>
<td>10</td>
<td>12</td>
<td>9</td>
</tr>
<tr>
<td>( C_{OUT} )</td>
<td>Output Capacitance</td>
<td>( V_{OUT} = 0 )</td>
<td>10</td>
<td>13</td>
<td>9</td>
</tr>
</tbody>
</table>

Notes:
1. This parameter is only sampled and not 100% tested.
2. \( T_{A} = +25^\circ C \), \( f = 1 \, MHz \).
PHYSICAL DIMENSIONS*
CDV028—28-Pin Ceramic Dual In-Line Package, UV Lens (measured in inches)

* For reference only. BSC is an ANSI standard for Basic Space Centering.

PD 028—28-Pin Plastic Dual In-Line Package (measured in inches)
REVISION SUMMARY FOR AM27C512

Revision I (May 1998)
Global
Changed formatting to match current data sheets.

Product Selector Guide
Added the -55 speed option for \( V_{CC} = 5.0 \, \text{V} \pm 10\% \).

Ordering Information—UV EPROM Products

Ordering Information—OTP EPROM Products
Valid Combinations: Added speed options for -55 with \( V_{CC} = 5.0 \, \text{V} \pm 5\% \) and -55 with \( V_{CC} = 5.0 \, \text{V} \pm 10\% \).

Revision J (January 1999)
Ordering Information
Added the 5% voltage tolerance information for ordering part numbers.

Revision J+1 (March 5, 1999)
Ordering Information
UV EPROM Products: Corrected the first row valid combination to DC5.

Revision J+2 (June 1, 1999)
Ordering Information
Corrected device organization to 64K x 8-Bit.

Absolute Maximum Ratings
Changed Note 1 reference to indicate that it pertains voltage on all pins. Corrected Note 1 to indicate that maximum input voltage is \( V_{CC} + 0.5 \, \text{V} \).

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